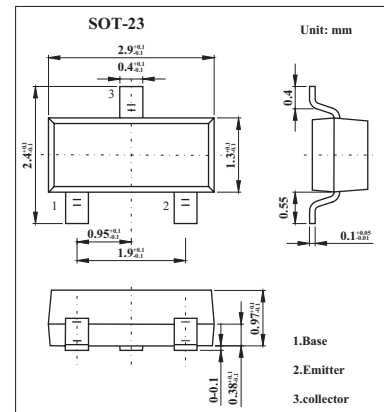


NPN Epitaxial Planar Silicon Transistor

2SD2028

■ Features

- With Zener diode (11 \pm 3V) between collector and base.
- Large current capacity.
- Low collector-to-emitter saturation voltage.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage, With Zener diode (11 \pm 3V)	V _{CB0}	8	V
Collector-emitter voltage, With Zener diode (11 \pm 3V)	V _{CEO}	8	V
Emitter-base voltage	V _{EBO}	5	V
Collector current	I _c	0.7	A
Collector current (pulse)	I _{CP}	1.5	A
Collector dissipation	P _c	200	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cutoff current	I _{cBO}	V _{CB} = 6V, I _E = 0			100	nA
Emitter cutoff current	I _{EBO}	V _{EB} = 4V, I _C = 0			100	nA
DC current Gain	h _{FE}	V _{CE} = 2V, I _C = 50mA	200		900	
Gain bandwidth product	f _T	V _{CE} = 2V, I _C = 50mA		200		MHz
Output capacitance	C _{ob}	V _{CB} = 5V, f = 1MHz		12		pF
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 100mA, I _B = 10mA		50	120	mV
Base-emitter saturation voltage	V _{BE(sat)}	I _C = 100mA, I _B = 10mA		0.8	1.2	V
Collector-to-base breakdown voltage	V _{(BR)CBO}	I _C = 100 μ A, I _E = 0	8	11	14	V
Collector-to-emitter breakdown voltage	V _{(BR)CEO}	I _C = 100 μ A, R _{BE} = ∞	8	11	14	V
Emitter-to-base breakdown voltage	V _{(BR)EBO}	I _E = 10 μ A, I _C = 0	5			V

■ hFE Classification

Marking	LT		
	6	7	8
hFE	200~400	300~600	450~900